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(54) Title: AUTOMATED DRY-IN DRY-OUT DUAL SIDE POLISHING OF SILICON SUBSTRATES WITH INTEGRATED SPIN RINCE DRY AND METROLOGY

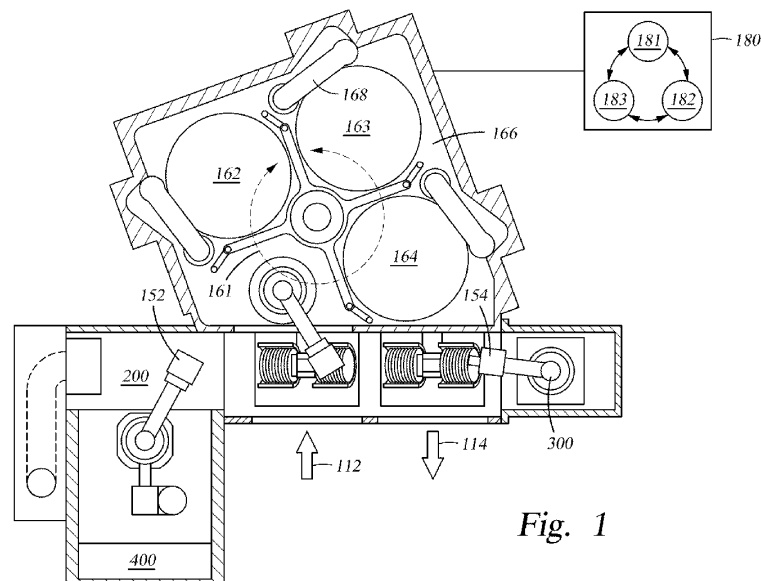


Fig. 1

(57) Abstract: A method and apparatus for polishing a substrate is disclosed herein. More specifically, the apparatus relates to an integrated CMP system for polishing substrates. The CMP system has a polishing station configured to polish substrates. A spin rinse dry (SRD) station configured to clean and dry the substrates. A metrology station configured to measure parameters of the substrates. A robot configured to move the substrate in to and out of the SRD station. And an effector rinse and dry (EBRD) station configured to clean and dry an end effector of the robot.

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